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PATENT & TRADEMARK OFFICE

Form PTO-1449 (Modified)	Atty. Docket No. 50422-7	Serial No. 10/761,275
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Applicant Steven E. Hill	
	Filing Date January 22, 2004	Group 2813

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER							DATE	NAME	CLASS	SUB CLASS	FIL.DATE IF APPROPRIATE
TN	AA	5	4	3	4	8	7	8	Jul 18, 1995	Lawandy	372	43	
	AB	6	2	9	4	4	0	1	Sept 25, 2001	Jacobson et al.	438	99	
	AC	0	0	1	7	6	5	7	Feb 14, 2002	Coffa et al.	257	200	
	AD	0	0	7	0	1	2	1	Jun 13, 2002	Nayfch et al.	205	549	
	AE	0	0	7	4	5	6	5	Jun 20, 2002	Flagan et al.	257	200	
	AF	0	1	6	3	0	0	3	Nov 7, 2002	Dal Negro et al.	257	79	

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		DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
													YES	NO
TN	AG	2	0	6	1	8	1	5	28.01.2002	WO	H01L	21/20	✓	

OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

TN	AH		A. Nakajima, et al.; MICROSTRUCTURE AND OPTICAL ABSORPTION PROPERTIES OS Si NANOCRYSTALS FABRICATED WITH LOW-PRESSURE CHEMICAL-VAPOR DEPOSITION; J. Appl. Phys., Vol. 80, No. 7, 1 October 1996, pp. 4006-4011.
	AI		Jeong Sook Ha, et al.; Er^{3+} PHOTOLUMINESCENCE FROM Er-DOPED AMORPHOUS SiO_x FILMS PREPARED BY PULSED LASER DEPOSITION AT ROOM TEMPERATURE: THE EFFECTS OF OXYGEN CONCENTRATION; Applied Physics Letters, Vol. 82, No. 20, 19 May 2003, pp. 3436-3438.
	AJ		Jung H. Shin, et al.; EFFECT OF HYDROGENATION ON ROOM-TEMPERATURE 1.54 μm Er^{3+} PHOTOLUMINESCENT PROPERTIES OF ERBIUM-DOPED SILICON-RICH SILICON OXIDE; Applied Physics Letters, Vol. 73, No. 25, 21 December 1998, pp. 3647-3649.
	AK		T.G. Kim, et al.; CONTROLLING THE FORMATION OF LUMINESCENT Si NANOCRYSTALS IN PLASMA-ENHANCED CHEMICAL VAPOR DEPOSITED SILICON-RICH SILICON OXIDE THROUGH ION IRRADIATION; Journal of Applied Physics, Vol. 91, No. 5, 1 March 2002, pp. 3236-3242.
	AL		M. Li, et al.; ELLIPSOMETRY INVESTIGATION OF NUCLEATION AND GROWTH OF ELECTRON CYCLOTRON RESONANCE PLASMA DEPOSITED SILICON FILMS; J. Vac. Sci. Technol. A 11(4) Jul/Aug 1993, pp. 1686-1691.
	AM		H.S. Bae, et al.; ELECTROLUMINESCENCE MECHANISM IN SiO_x LAYERS CONTAINING RADIATIVE CENTERS; Journal of Applied Physics, Vol. 91, No. 7, 1 April 2002, pp. 4078-4081.
	AN		Minoru Fujii, et al.; 1.54 μm PHOTOLUMINESCENCE OF Er^{3+} DOPED INTO SiO_2 FILMS CONTAINING Si NANOCRYSTALS: EVIDENCE FOR ENERGY TRANSFER FROM Si NANOCRYSTALS TO Er^{3+}; Appl. Phys. Lett. 71 (9), September 1997, pp. 1198-1200.
	AO		Giorgia Franzò, et al.; ENHANCED RARE EARTH LUMINESCENCE IN SILICON NANOCRYSTALS; Materials Science and Engineering B69-70, 2000, pp. 335-339.

EXAMINER	DATE CONSIDERED
T. Nguyen	10/28/05

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TN	AP		Giorgia Franzò, et al.; Er^{3+} IONS-Si NANOCRYSTALS INTERACTIONS AND THEIR EFFECTS ON THE LUMINESCENCE PROPERTIES; Applied Physics Letters, Vol. 76, No. 16, 17 April 2000, pp. 2167-2169.
	AQ		Se-Young Seo, and Jung H. Shin; EXCITON-ERBIUM COUPLING AND THE EXCITATION DYNAMICS OF Er^{3+} IN ERBIUM-DOPED SILICON-RICH SILICON OXIDE; Applied Physics Letters, Vol. 78, No. 18, 30 April 2001, pp. 2709-2711.
	AR		Jung H. Shin, et al.; PHOTOLUMINESCENCE EXCITATION SPECTROSCOPY OF ERBIUM-DOPED SILICON-RICH SILICON OXIDE; Applied Physics Letters, Vol. 76, No. 15, 10 April 2000, pp. 1999-2001.
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	AW		Jung H. Shin, et al.; COMPOSITION DEPENDENCE OF ROOM TEMPERATURE 1.54 μm Er^{3+} LUMINESCENCE FROM ERBIUM-DOPED SILICON: OXYGEN THIN FILMS DEPOSITED BY ELECTRON CYCLOTRON RESONANCE PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION; Applied Physics Letters, Vol. 72, No. 9, 2 March 1998, pp. 1092-1094.
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	AY		G. Franzò, et al.; ELECTROLUMINESCENCE OF SILICON NANOCRYSTALS IN MOS STRUCTURES; Appl. Phys. A, Materials Science & Processing, 74, (2002), pp. 1-5.
	AZ		A. Irrera, et al.; EXCITATION AND DE-EXCITATION PROPERTIES OF SILICON QUANTRUM DOTS UNDER ELECTRICAL PUMPING; Applied Physics Letters, Vol. 81, No. 10, 2 September 2002, pp. 1866-1868.
	aa		P.S. Andry, et al.; GROWTH OF Er-DOPED SILICON USING METALORGANICS BY PLASMA-ENHANCED CHEMICAL VAPOR DEPOSITION; J. Appl. Phys. 80 (1), 1 July 1996, pp. 551-558.
	ab		Kei Watanabe, et al.; RESONANT EXCITATION OF Er^{3+} BY THE ENERGY TRANSFER FROM Si NANOCRYSTALS; Journal of Applied Physics, Vol. 90, No. 9, 1 November 2001, pp. 4761-4767.
	ac		J. De la Torre, et al.; OPTICAL PROPERTIES OF SILICON NANOCRYSTAL LEDs; Elsevier Science B.V., Physica E, 2002, pp. 326-330.

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TN	AA	5,667,905	1997.09.16	Campisano, Salvatore Ugo et al.			
	AB	6,255,669	2001.07.03	Birkhahn, Ronald H. et al.			
	AC	US 2003/034486	2003.02.20	Korgel, Brian A.			
	AD	US 2002/048289	2002.04.25	Atanackovic, Petar B et al.			
	AE	US 2004/183087	2004.09.23	Gardner, Donald S.			
	AF	5,422,907	1995.06.06	Bhargava, Raneshwar N.			
	AG	5,637,258	1997.06.10	Goldburt, Efim T. et al.			

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TN	AH	101 04 193	2002.08.01	DE				
	AI	2001 203382	2001.07.11	JP				
	AJ	1 134 799	2001.09.19	EP				
	AK	WO 02/061815	2002.08.08	DE				
	AL	0 650 200	1995.04.26	EP				

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TN	AM	Orlov, L.K. et al.	COMPARITIVE ANALYSIS OF LIGHT EMMITTING PROPERTIES OF Si:Er AND $Ge/Si_{1-x}Ge_x$ EPITAXIAL STRUCTURES OBTAINED BY MBE METHOD. *Gettering and Defect Engineering in Semiconductor Technology, Solid State Phenomena (FORMERLY Part B of "Diffusion and Defect Data [0377-6883]).* Vol 69 until 70, 1999. Pages 377-382. ISSN:1012-0394.
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	AO	Yun, F. et al.	ROOM TEMPERATURE SINGLE-ELECTRON NARROW-CHANNEL MEMORY WITH SILICONNANODOTS EMBEDDED IN SiO_2 MATRIX. *Japanese Journal of Applied Physics.* Publication Office Japanese Journal of Applied Physics. Vol. 39, no. 8A Part II. August 1, 2000. Tokyo, Japan. Pages L792- L795.

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TN	AP	Rozo, C. et al.	SPECTOSCOPIC STUDY OF RARE EARTH DOPED NANO-CRYSTALLINE SILICON IN SIO2 FILMS. *Quantum Confined Semiconductor Nanostructures. Symposium (Mater. Res. Soc. Symposium Proceedings Vol. 737)* Mater Res. Soc Warrendale, Pa, USA, 2003. Pages 517-522, XP 002310621. ISBN:1-55899-674-5
	AQ	Fujii, Minoru et al.	EXCITATION OF INTRA-4*f* SHELL LUMINESCENCE OF Yb^{3+} BY ENERGY TRANSFER FROM Si NANOCRYSTALS. *Applied Physics Letters.* American Institute of Physics. New York, USA. Vol. 73, no. 21. 23 November 1998, Pages 3108-3110, XP 012021485. ISSN: 0003-6951.
	AR	Pacifici, D. et al.	ERBIUM-DOPED Si NANOCRYSTALS: OPTICAL PROPERTIES AND ELECTOLUMINESCENT DEVICES. *Physica E.* Elsevier netherlands, Vol. 16, no. 3-4, March 2003. Pages 331-340, XP 002310622. ISSN: 1386-9477.

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